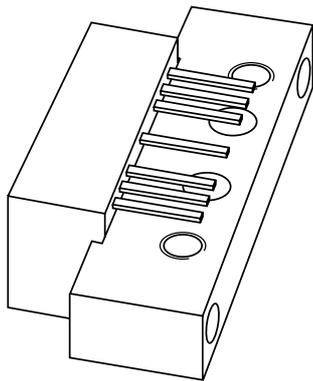


DATA SHEET



BGY67

**200 MHz, 22 dB gain reverse
amplifier**

Product specification
Supersedes data of 1997 Apr 15

2001 Oct 18

200 MHz, 22 dB gain reverse amplifier

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FEATURES

- Excellent linearity
- Extremely low noise
- Silicon nitride passivation
- Rugged construction
- TiPtAu metallized crystals ensure optimal reliability.

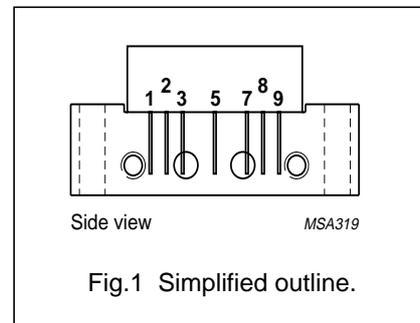
DESCRIPTION

Hybrid amplifier module for CATV systems operating over a frequency range of 5 to 200 MHz at a voltage supply of +24 V (DC). The device is intended as a reverse amplifier for use in two way systems.

PINNING - SOT115J

PIN	DESCRIPTION
1	input
2	common
3	common
5	+V _B
7	common
8	common
9	output

PIN CONFIGURATION



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 10 MHz	21.5	–	22.5	dB
I _{tot}	total current consumption (DC)	V _B = +24 V	–	215	230	mA

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _i	RF input voltage	–	65	dBmV
T _{stg}	storage temperature	–40	+100	°C
T _{mb}	mounting base operating temperature	–20	+90	°C

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CHARACTERISTICS

Table 1 Bandwidth 5 to 200 MHz; $T_{mb} = 30\text{ °C}$; $Z_S = Z_L = 75\ \Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G_p	power gain	$f = 10\text{ MHz}$	21.5	–	22.5	dB
SL	slope cable equivalent	$f = 5\text{ to }200\text{ MHz}$	-0.2	–	+0.5	dB
FL	flatness of frequency response	$f = 5\text{ to }200\text{ MHz}$	–	–	± 0.2	dB
S_{11}	input return losses	$f = 5\text{ to }200\text{ MHz}$	20	–	–	dB
S_{22}	output return losses	$f = 5\text{ to }200\text{ MHz}$	20	–	–	dB
CTB	composite triple beat	22 channels flat; $V_o = 50\text{ dBmV}$; measured at 175.25 MHz	–	–	-67	dB
X_{mod}	cross modulation	22 channels flat; $V_o = 50\text{ dBmV}$; measured at 55.25 MHz	–	–	-60	dB
d_2	second order distortion	$V_o = 50\text{ dBmV}$; note 1	–	–	-67	dB
V_o	output voltage	$d_{im} = -60\text{ dB}$; note 2	67	–	–	dBmV
		$d_{im} = -60\text{ dB}$; note 3	64	–	–	dBmV
F	noise figure	$f = 200\text{ MHz}$	–	–	5.5	dB
I_{tot}	total current consumption	DC value; $V_B = +24\text{ V}$; note 4	–	215	230	mA

Notes

- $f_p = 83.25\text{ MHz}$; $V_p = 50\text{ dBmV}$;
 $f_q = 109.25\text{ MHz}$; $V_q = 50\text{ dBmV}$;
measured at $f_p + f_q = 192.5\text{ MHz}$.
- Measured according to DIN45004B;
 $f_p = 35.25\text{ MHz}$; $V_o = V_p$;
 $f_q = 42.25\text{ MHz}$; $V_q = V_o - 6\text{ dB}$;
 $f_r = 44.25\text{ MHz}$; $V_r = V_o - 6\text{ dB}$;
measured at $f_p + f_q - f_r = 33.25\text{ MHz}$.
- Measured according to DIN45004B;
 $f_p = 187.25\text{ MHz}$; $V_o = V_p$;
 $f_q = 194.25\text{ MHz}$; $V_q = V_o - 6\text{ dB}$;
 $f_r = 196.25\text{ MHz}$; $V_r = V_o - 6\text{ dB}$;
measured at $f_p + f_q - f_r = 185.25\text{ MHz}$.
- The module normally operates at $V_B = +24\text{ V}$, but is able to withstand supply transients up to $+30\text{ V}$.

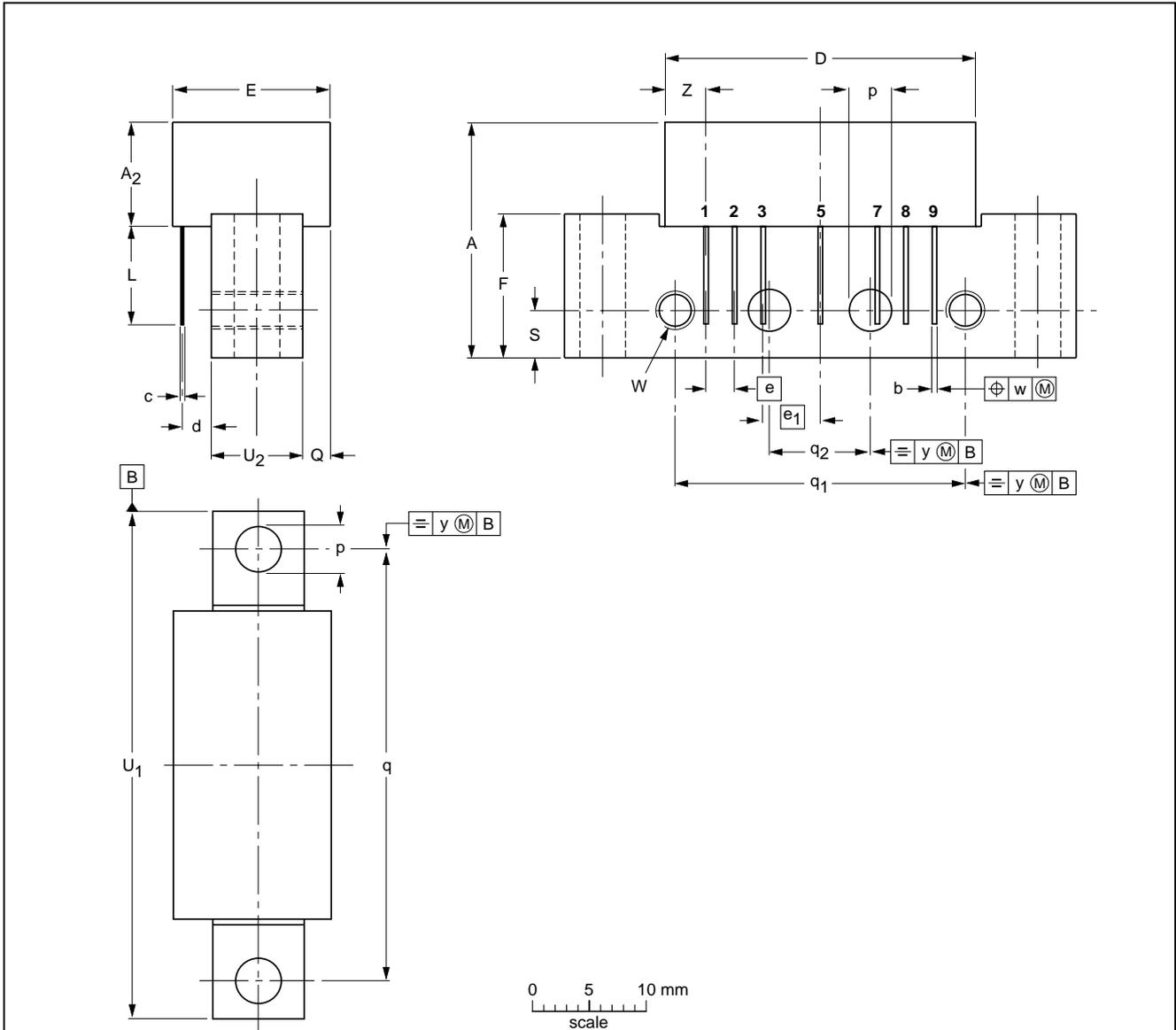
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PACKAGE OUTLINE

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₂ max.	b	c	D max.	d max.	E max.	e	e ₁	F	L min.	p	Q max.	q	q ₁	q ₂	S	U ₁ max.	U ₂	W	w	y	Z max.
mm	20.8	9.1	0.51 0.38	0.25	27.2	2.54	13.75	2.54	5.08	12.7	8.8	4.15 3.85	2.4	38.1	25.4	10.2	4.2	44.75	8	6-32 UNC	0.25	0.1	3.8

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT115J						99-02-06

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DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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NOTES

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NOTES

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